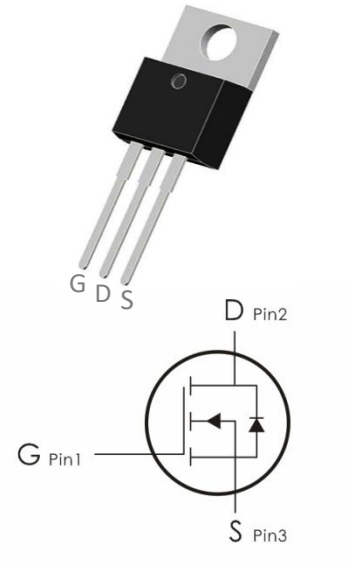
Description：

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features：

1) V_{DS}=68V,I_D=80A,$R_{DS(ON)}$<8mΩ @V_{GS}=10V（Typ：6.6mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
PS008NG-B	S008N-B	TO- 220	50 pcs/Tube

Absolute Maximum Ratings： (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	68	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	80	A
	Continuous Drain Current-T_C=100℃	56	
P_D	Power Dissipation	72	W
I_{DM}	Pulsed Drain Current[1]	320	A
E_{AS}	Single pulse avalanche energy[2]	206	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	1.7	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	68	℃/W

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	68	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=68V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	2	3.09	4	V
$R_{DS(ON)}$	Drain-Source On Resistance[3]	V_{GS}=10V,I_D=30A	---	6.6	8	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=35V, V_{GS}=0V, f=1MHz	---	5389	---	pF
C_{oss}	Output Capacitance		---	262	--	
C_{rss}	Reverse Transfer Capacitance		---	208	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=35V, I_D=30A, R_{ENG}=3Ω ,V_{GS}=10V	---	21	---	ns
t_r	Rise Time		---	31.5	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	47	---	ns
t_f	Fall Time		---	14.7	---	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=35V, I_D=30A	---	98	---	nC
Q_{gs}	Gate-Source Charge		---	31	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	25	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=30A	---	---	1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	80	A
I_{SM}	Pulsed Drain Current		---	---	320	A
Trr	Reverse Recovery Time	I_F=28A,T_J=25℃ dI/dt=300A/us	---	30	---	ns
Qrr	Reverse Recovery Charge		---	41.8	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition : TJ=25℃,VDD=35V,V_G=10V,L=0.5mH
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics：

(T_C=25℃ unless otherwise noted)

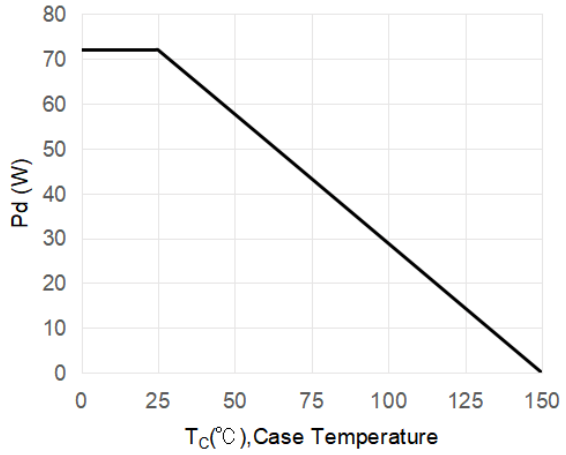


Figure 1: Power De-rating

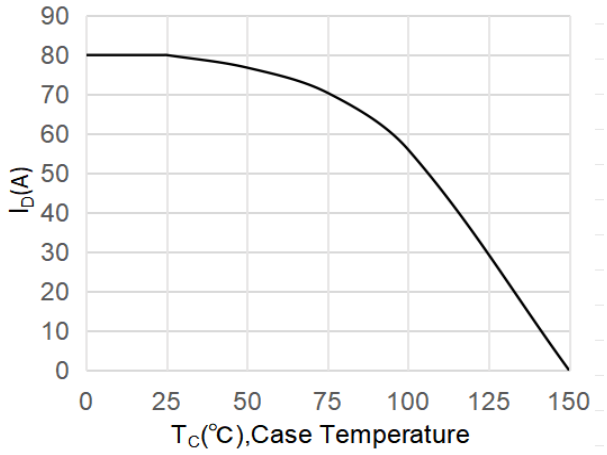


Figure 2: Current De-rating

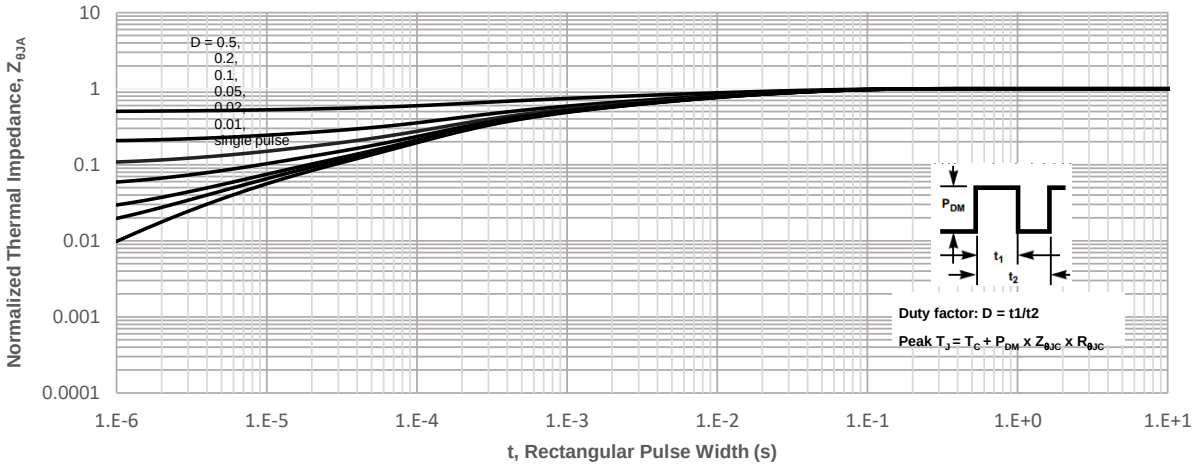


Figure 3: Normalized Maximum Transient Thermal Impedance

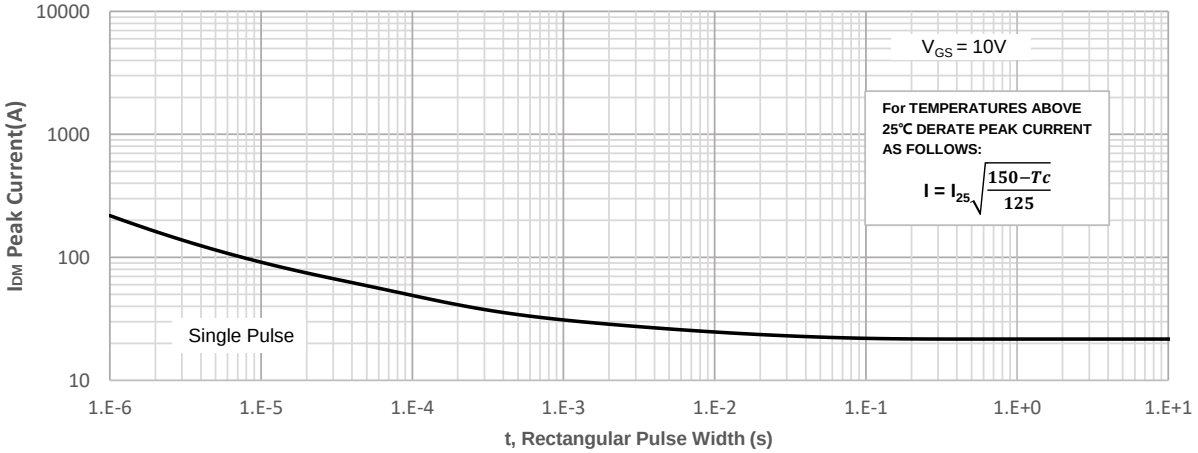


Figure 4: Peak Current Capacity

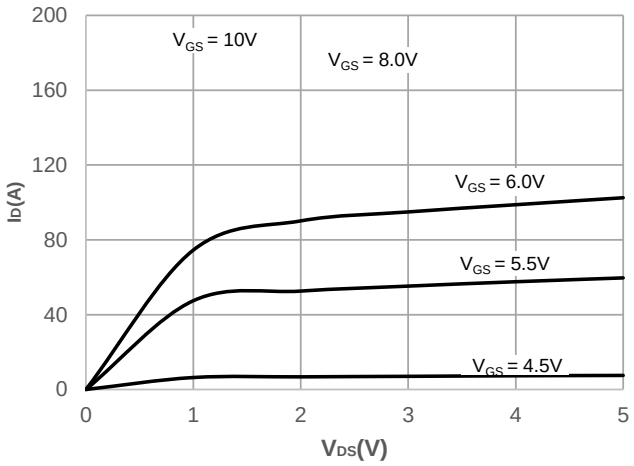


Figure 5: Output Characteristics

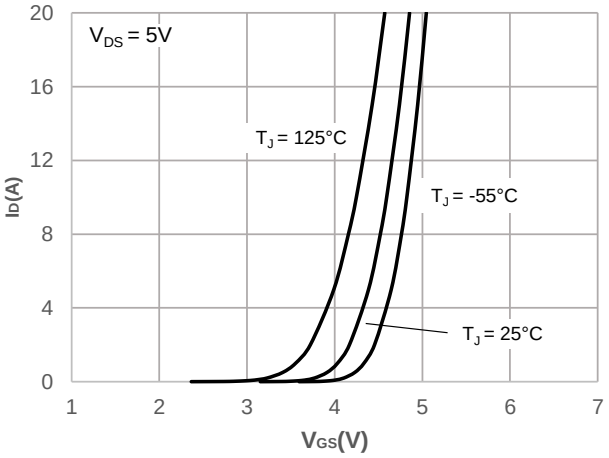


Figure 6: Typical Transfer Characteristics

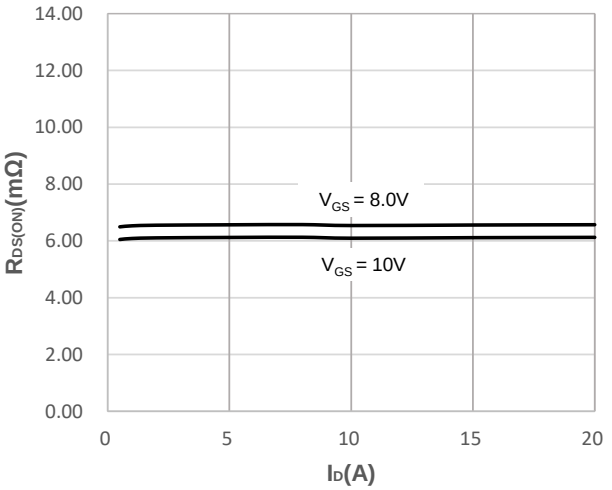


Figure 7: On-resistance vs. Drain Current

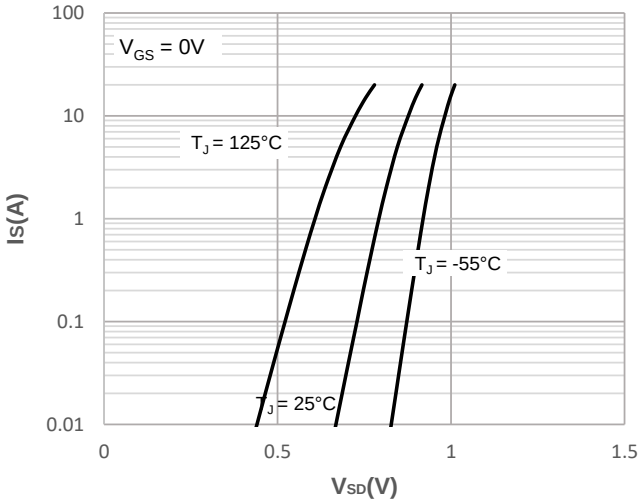


Figure 8: Body Diode Characteristics

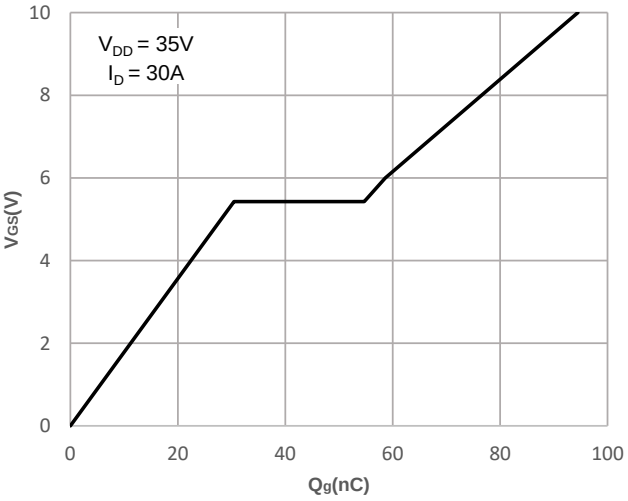


Figure 9: Gate Charge Characteristics

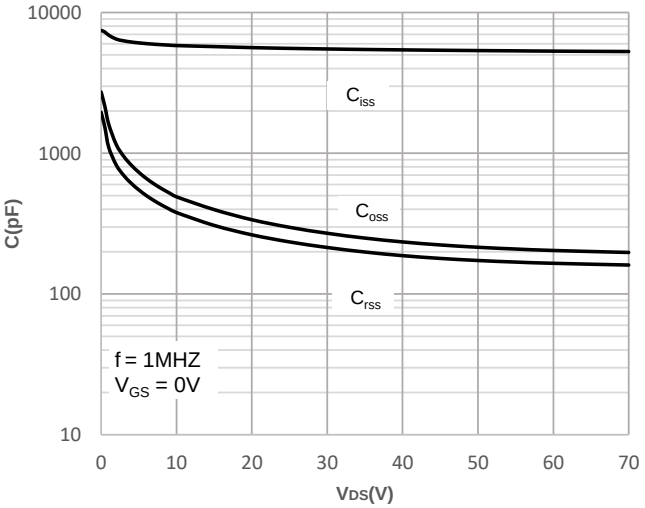


Figure 10: Capacitance Characteristics

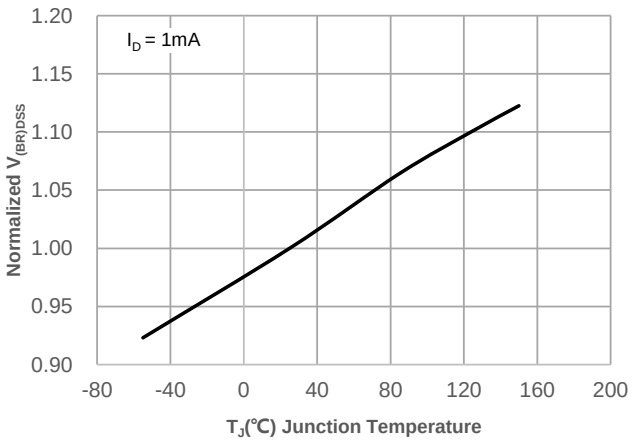


Figure 11: Normalized Breakdown voltage vs. Junction Temperature

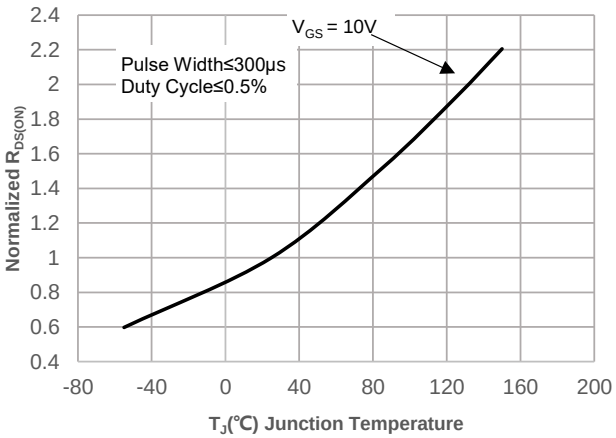


Figure 12: Normalized on Resistance vs. Junction Temperature

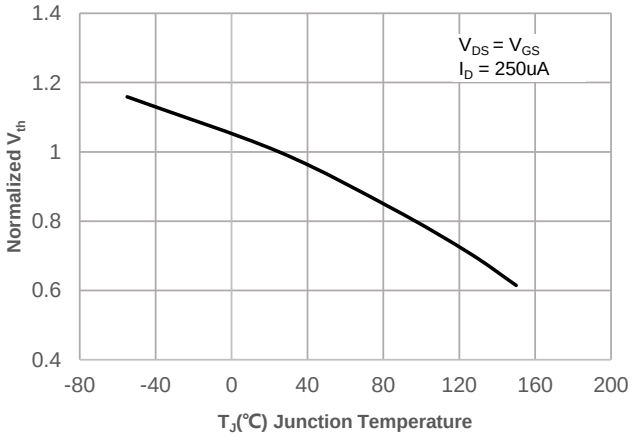


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

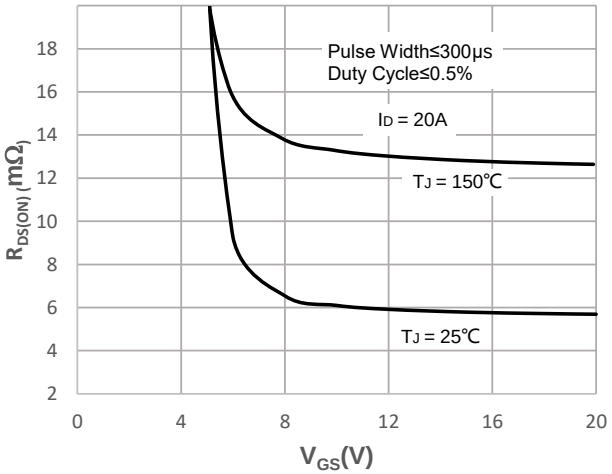


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

20

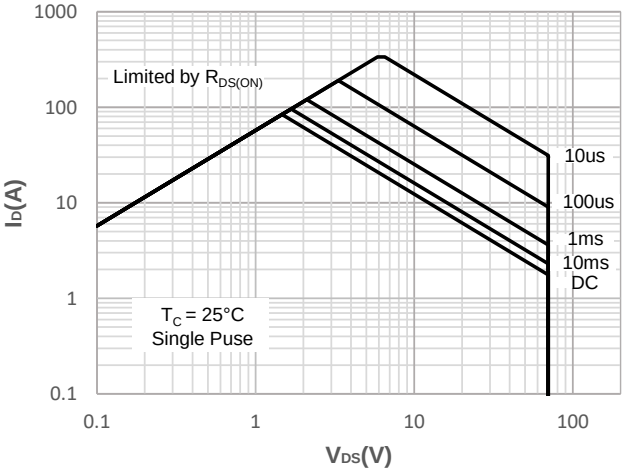
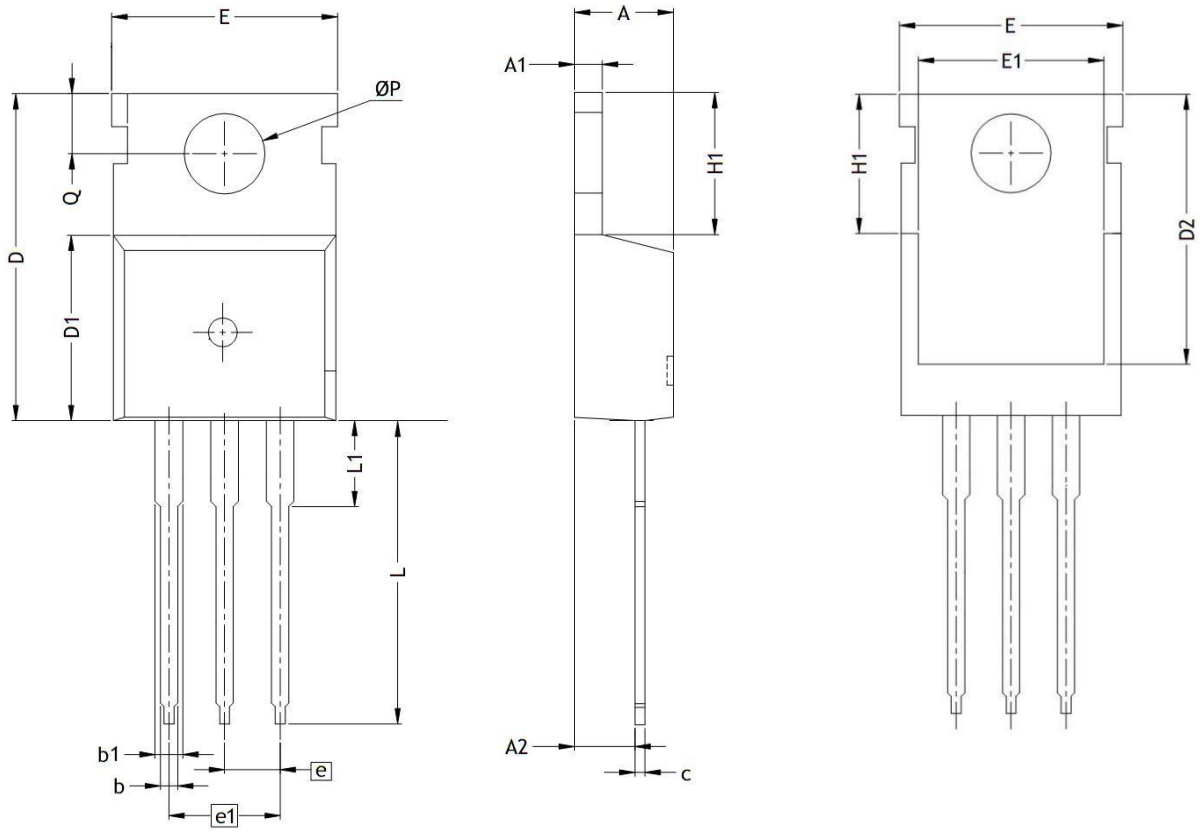


Figure 15: Maximum Safe Operating Area

TO-220 Package Information：



UNIT：mm

SYMBOLS	A	A1	A2	b	b1	c	D	D1	D2	E	E1	e
MIN	4.25	1.25	2.35	0.7	1.15	0.45	14.35	8.80	13.05	9.90	7.85	2.540
MAX	4.65	1.35	2.55	0.9	1.75	0.60	15.95	9.50	13.65	10.35	8.85	BSC
SYMBOLS	e1	H1	L	L1	Q	ϕP						
MIN	5.080	6.30	12.85	2.85	2.70	3.50						
MAX	BSC	6.65	13.50	3.25	2.90	3.70						

Marking Information：

①. Doingter LOGO

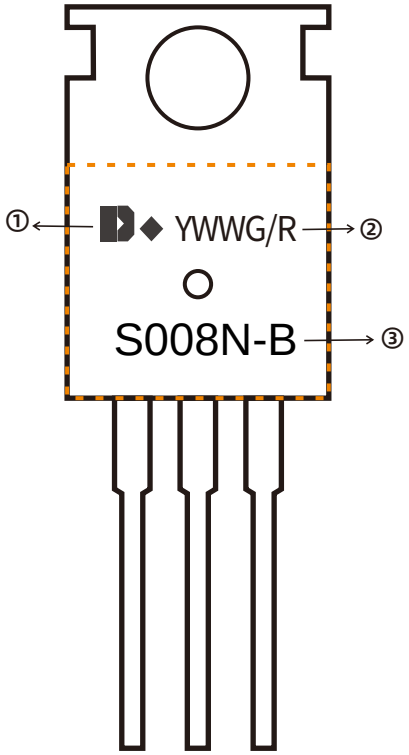
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



Previous Version

Version	Date	Subjects (major changes since last revision)
1.1	2026-05-16	Release of final version

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